| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| 1 | 1384 | phase near3 chang$3 near3 device | USPAT; US-PGPUB | 2003/10/31 06:39 |
| 2 | 564 | (phase near3 chang$3 near3 device) and (gate electrode) | USPAT; US-PGPUB | 2003/10/31 06:39 |
| 3 | 174 | ((phase near3 chang$3 near3 device) and (gate electrode)) and etch$3 | USPAT; US-PGPUB | 2003/10/31 06:24 |
| 4 | 732 | phase near3 chang$3 near3 device | EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 06:39 |
| 5 | 53 | (phase near3 chang$3 near3 device) and (gate electrode) | EPO; JPO; DERWENT; IBM_TDB | 2003/10/31 06:39 |
| - | 2202 | tapered near5 electrode | USPAT; US-PGPUB | 2003/10/31 06:23 |
| - | 112 | (tapered near5 electrode) and trench | USPAT; US-PGPUB | 2003/10/30 12:03 |
| - | 1182 | tapered near5 electrode | EPO; JPO; DERWENT; IBM_TDB | 2003/10/30 12:02 |
| - | 0 | (tapered near5 electrode) and trench | USPAT; US-PGPUB | 2003/10/30 12:02 |
| - | 0 | (tapered near5 electrode) and (trench onen$3 recess hole via contact) | USPAT; US-PGPUB | 2003/10/30 12:03 |
| - | 2000 | (tapered near5 electrode) and (trench onen$3 recess hole via contact) | USPAT; US-PGPUB | 2003/10/30 15:36 |
| - | 1645 | tapered near5 electrode | US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2003/10/30 15:17 |
| - | 410 | (tapered near5 electrode) and (trench onen$3 recess hole via contact) | EPO; JPO; DERWENT; IBM_TDB | 2003/10/30 15:32 |
| - | 77 | ((tapered near5 electrode) and (trench onen$3 recess hole via contact)) and (semiconductor wafer) | EPO; JPO; DERWENT; IBM_TDB | 2003/10/30 15:32 |
| - | 2931 | tapered near5 (electrode gate) | USPAT; US-PGPUB | 2003/10/30 15:36 |
| - | 2649 | (tapered near5 (electrode gate)) and (trench onen$3 recess hole via contact) | USPAT; US-PGPUB | 2003/10/30 15:36 |
| - | 1307 | ((tapered near5 (electrode gate)) and (trench onen$3 recess hole via contact)) and (semiconductor wafer substrate) | USPAT; US-PGPUB | 2003/10/30 15:37 |
| - | 984 | (((tapered near5 (electrode gate)) and (trench onen$3 recess hole via contact)) and (semiconductor wafer substrate)) and etch$3 | USPAT; US-PGPUB | 2003/10/30 15:37 |
| - | 779 | ((((tapered near5 (electrode gate)) and (trench onen$3 recess hole via contact)) and (semiconductor wafer substrate)) and etch$3) and mask | USPAT; US-PGPUB | 2003/10/30 15:45 |
| - | 4471 | phase near10 change near10 (device memory) | USPAT; US-PGPUB | 2003/10/30 15:45 |
| - | 7 | (phase near10 change near10 (device memory)) and (tapered near5 (electrode gate)) | USPAT; US-PGPUB | 2003/10/30 15:46 |
| - | 4825 | (gate electrode) near10 (etch$3 pattern$3) near100 mask near100 (trench hole open$3 via contact recess groove) | USPAT; US-PGPUB | 2003/10/30 18:56 |
| - | 1481 | ((gate electrode) near10 (etch$3 pattern$3) near100 mask near100 (trench hole open$3 via contact recess groove)) and charge | USPAT; US-PGPUB | 2003/10/30 18:56 |
| - | 1471 | (((gate electrode) near10 (etch$3 pattern$3) near100 mask near100 (trench hole open$3 via contact recess groove)) and charge) and (semiconductor wafer substrate) | USPAT; US-PGPUB | 2003/10/30 18:17 |
| - | 2095 | (gate electrode) near10 (etch$3 pattern$3) near100 mask near100 (trench hole open$3 via contact recess groove) | EPO; JPO; DERWENT; IBM_TDB | 2003/10/30 18:56 |
| - | 45 | ((gate electrode) near10 (etch$3 pattern$3) near100 mask near100 (trench hole open$3 via contact recess groove)) and charge | EPO; JPO; DERWENT; IBM_TDB | 2003/10/30 18:57 |